

RB500V-40

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

Features

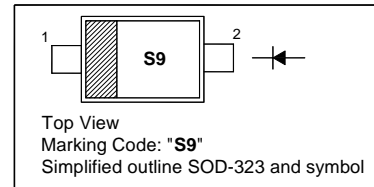
- Small surface mounting type
- Low I_R
- High reliability

Applications

- Low current rectification

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



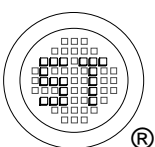
Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	45	V
Power Dissipation	P_{tot}	200	mW
Reverse Voltage	V_R	40	V
Mean Rectifying Current	I_O	0.1	A
Peak Forward Surge Current (60 Hz for 1 Cyc.)	I_{FSM}	1	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	45	-	-	V
Forward Voltage at $I_F = 10\text{ mA}$	V_F	-	-	0.45	V
Reverse Current at $V_R = 10\text{ V}$	I_R	-	-	1	μA
Capacitance Between Terminals at $V_R = 10\text{ V}$, $f = 1\text{ MHz}$	C_T	-	6	-	pF

Note: ESD sensitive product handling required.



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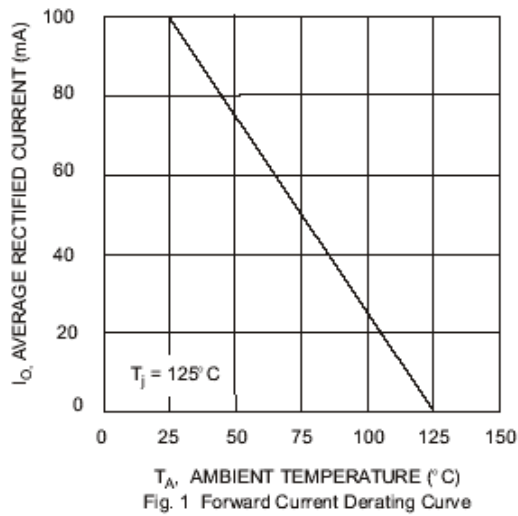


Fig. 1 Forward Current Derating Curve

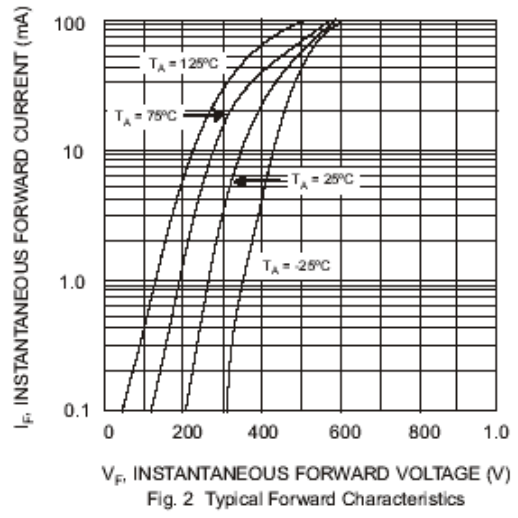


Fig. 2 Typical Forward Characteristics

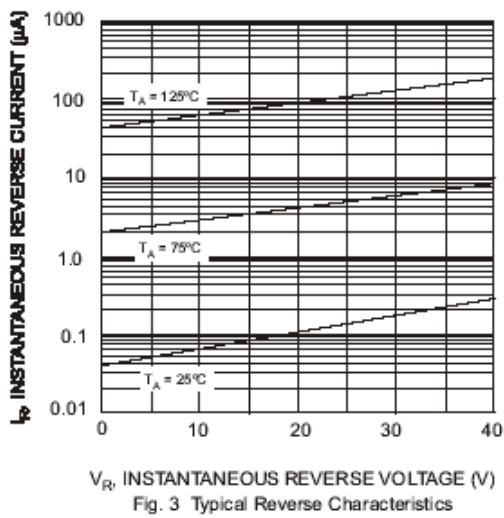


Fig. 3 Typical Reverse Characteristics

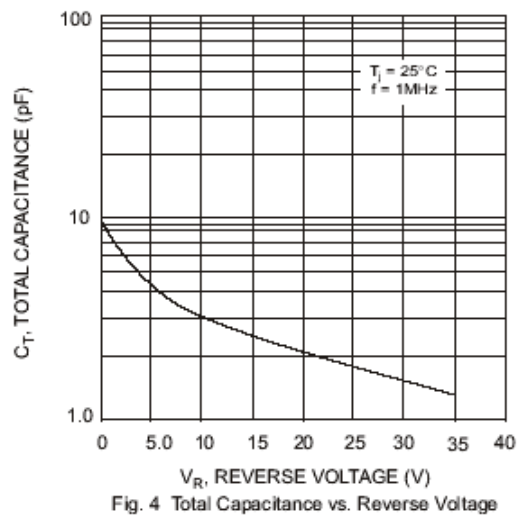
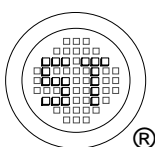


Fig. 4 Total Capacitance vs. Reverse Voltage



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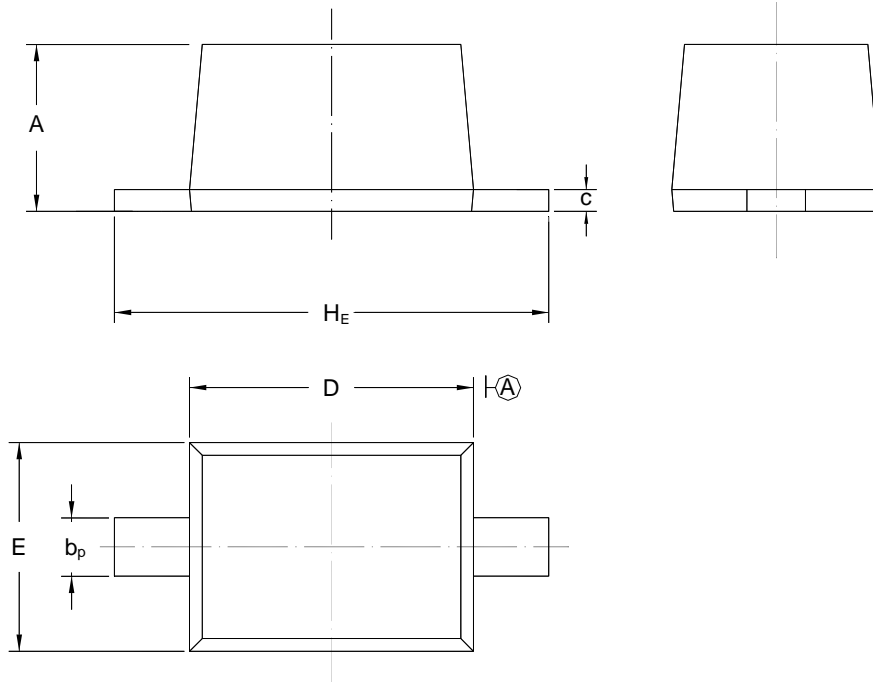


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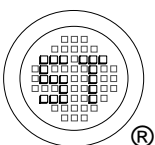
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b _p	C	D	E	H _E
mm	1.10 0.80	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30



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